The evolution of deep traps in the MOS CCDs











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MOS1 CC Offsets at Al Kα as Calculated by EMOS Package

Offset < -100 eV -100 < Offset < -50 50 < Offset < 100 Offset > 100







MOS2 CC Offsets at Al Kα as Calculated by EMOS Package

Offset < -100 eV -100 < Offset < -50 50 < Offset < 100 Offset > 100







MOS1 CC Offsets at Al Kα as Calculated by EMOS Package

Offset < -100 eV -100 < offset < -50 50 < Offset < 100 Offset > 100

Number of offsets versus year since launch







MOS2 CC Offsets at Al Kα as Calculated by EMOS Package

Offset < -100 eV -100 < offset < -50 50 < Offset < 100 Offset > 100

Number of offsets versus year since launch







0709/0160362701 A Pattern 0 -20 < Offset < 20 eV Offset < -100 eV

Post-Cooling $CCD = -120^{\circ}C$



MPE 25/03/2014





0709/0160362701 Mn Pattern 0 -20 < Offset < 20 eV Offset < -100 eV **Post-Cooling**

 $CCD = -120^{\circ}C$

Note: No strong **Energy dependence!**



MPE 25/03/2014



SWIFT XRT energy dependent traps: (same CCD as MOS, run warmer by ~50-70°C)

```
Off(E) = Off(E_{REF}) \times (E / E_{REF})^{\alpha}
```

$$\alpha = - \begin{cases} 0.80, E < E_{REF} \\ 0.75, E > E_{REF} \end{cases}$$

Using this formula, a 50 eV trap at Al K_{α} (1.49 keV) would have a depth of 142 eV at Mn K_{α} (5.9 keV),

a difference of 92 eV! - Not observed in EPIC-MOS







MOS1 CC 0533/0156960501 A Pattern 0 -20 < Offset < 20 eV Offset < -100 eV

Pre-Cooling $CCD = -100^{\circ}C$



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MOS1 CC 0533/0156960501 Mn Pattern 0 -20 < Offset < 20 eV Offset < -100 eV **Pre-Cooling** $CCD = -100^{\circ}C$

Note: No strong Energy dependence!







MOS







MOS1 CC 0709/0160362701 Mn Pattern 0-12 -20 < Offset < 20 eV Offset < -100 eV **Post-Cooling** $CCD = -120^{\circ}C$ Note: Reconstruction for multi-pixel events not so good





Summary:

Rate of generation of traps on central CCDs very different. MOS1 CCD1 >> MOS2 CCD1

Currently around ~10% of columns of MOS1, CCD1 affected by a deep trap

Good news: no strong energy dependence between AI and Mn. Need to check at low energies

But "single pixel energy trap model" breaks down for multipixel events...what to do about this??



